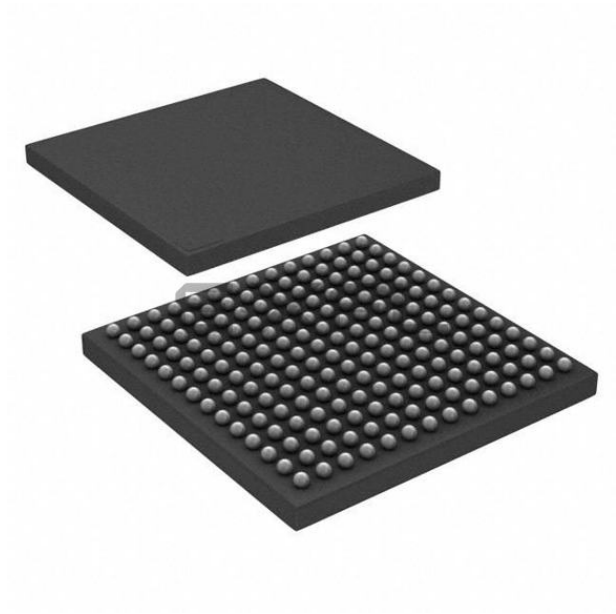
AMD Xilinx - XC7S6-2FTGB196C Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	6000
Total RAM Bits	184320
Number of I/O	100
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	196-LBGA, CSPBGA
Supplier Device Package	196-CSBGA (15x15)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7s6-2ftgb196c

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ[1]	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin.	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested).	–	–	15	µA
C_{IN}[2]	Die input capacitance at the pad.	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 3.3V.	90	–	330	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 2.5V.	68	–	250	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.8V.	34	–	220	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.5V.	23	–	150	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.2V.	12	–	120	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	68	–	330	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state.	–	–	25	mA
I_{BATT}[3]	Battery supply current.	–	–	150	nA
R_{IN_TERM}[4]	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_40).	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_50).	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_60).	44	60	83	Ω
n	Temperature diode ideality factor.	–	1.010	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. This measurement represents the die capacitance at the pad, not including the package.
3. Maximum value specified for worst case process at 25°C.
4. Termination resistance to a V_{CCO}/2 level.

Table 4: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HR I/O Banks(1)(2)**

AC Voltage Overshoot	% of UI at –40°C to 125°C	AC Voltage Undershoot	% of UI at –40°C to 125°C
V_{CCO} + 0.55	100	–0.40	100
		–0.45	61.7
		–0.50	25.8
		–0.55	11.0
V_{CCO} + 0.60	46.6	–0.60	4.77
V_{CCO} + 0.65	21.2	–0.65	2.10
V_{CCO} + 0.70	9.75	–0.70	0.94
V_{CCO} + 0.75	4.55	–0.75	0.43
V_{CCO} + 0.80	2.15	–0.80	0.20
V_{CCO} + 0.85	1.02	–0.85	0.09
V_{CCO} + 0.90	0.49	–0.90	0.04
V_{CCO} + 0.95	0.24	–0.95	0.02

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. The peak voltage of the overshoot or undershoot, and the duration above V_{CCO} + 0.20V or below GND – 0.20V, must not exceed the values in this table.

Table 5: **Typical Quiescent Supply Current(1)(2)(3)**

Symbol	Description	Device	Speed Grade						Units
			1.0V					0.95V	
			-2C	-2I	-1C	-1I	-1Q	-1LI	
I_{CCINTQ}	Quiescent V_{CCINT} supply current.	XC7S6	36	36	36	36	36	32	mA
		XC7S15	36	36	36	36	36	32	mA
		XC7S25	48	48	48	48	48	43	mA
		XC7S50	95	95	95	95	95	59	mA
		XC7S75	148	148	148	148	148	134	mA
		XC7S100	148	148	148	148	148	134	mA
		XA7S6	N/A	36	N/A	36	36	N/A	mA
		XA7S15	N/A	36	N/A	36	36	N/A	mA
		XA7S25	N/A	48	N/A	48	48	N/A	mA
		XA7S50	N/A	95	N/A	95	95	N/A	mA
		XA7S75	N/A	148	N/A	148	148	N/A	mA
		XA7S100	N/A	148	N/A	148	148	N/A	mA

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 8: **SelectIO DC Input and Output Levels**(1)(2)(3)

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_II	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSTL_II_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.10	–0.10
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVCMOS15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	Note 5	Note 5
LVCMOS18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 6	Note 6
LVCMOS25	–0.300	0.7	1.700	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVCMOS33	–0.300	0.8	2.000	3.450	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVTTL	–0.300	0.8	2.000	3.450	0.400	2.400	Note 6	Note 6
MOBILE_DDR	–0.300	20% V_{CCO}	80% V_{CCO}	V_{CCO} + 0.300	10% V_{CCO}	90% V_{CCO}	0.10	–0.10
PCI33_3	–0.400	30% V_{CCO}	50% V_{CCO}	V_{CCO} + 0.500	10% V_{CCO}	90% V_{CCO}	1.50	–0.50
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	13.00	–13.00
SSTL135_R	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.90	–8.90
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	13.00	–13.00
SSTL15_R	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	8.90	–8.90
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	8.00	–8.00
SSTL18_II	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.600	V_{CCO}/2 + 0.600	13.40	–13.40

Notes:

1. Tested according to relevant specifications.
2. 3.3V and 2.5V standards are only supported in HR I/O banks.
3. For detailed interface specific DC voltage levels, see the *7 Series FPGAs SelectIO Resources User Guide* (UG471) [Ref 3].
4. Supported drive strengths of 4, 8, or 12 mA in HR I/O banks.
5. Supported drive strengths of 4, 8, 12, or 16 mA in HR I/O banks.
6. Supported drive strengths of 4, 8, 12, 16, or 24 mA in HR I/O banks.

AC Switching Characteristics

All values represented in this data sheet are based on the speed specifications from the Vivado® Design Suite as outlined in Table 12.

Table 12: **Speed Specification Version By Device**

2018.2.1	Device
1.23	XC7S6, XC7S15, XC7S25, XC7S50, XC7S75, XC7S100
1.16	XA7S6, XA7S15, XA7S25, XA7S50, XA7S75, XA7S100

Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows.

Advance Product Specification

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary Product Specification

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Production Product Specification

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to Production before faster speed grades.

Testing of AC Switching Characteristics

Internal timing parameters are derived from measuring internal test patterns. All AC switching characteristics are representative of worst-case supply voltage and junction temperature conditions.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Spartan-7 FPGAs.

Table 15: **Networking Applications Interface Performances *(Cont'd)***

Description	V_{CCINT} Operating Voltage, Speed Grade, and Temperature Range			Units
	1.0V		0.95V	
	-2C/-2I	-1C/-1I/-1Q	-1LI	
DDR LVDS receiver(1)	1250	950	950	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications where specific dynamic phase-alignment (DPA) algorithms dominate deterministic performance.

Table 16: **Maximum Physical Interface (PHY) Rate for Memory Interface IP available with the Memory Interface Generator(1)**

Memory Standard	V_{CCINT} Operating Voltage, Speed Grade, and Temperature Range			Units
	1.0V		0.95V	
	-2C/-2I	-1C/-1I/-1Q	-1LI	
4:1 Memory Controllers				
DDR3	800(2)	667	667	Mb/s
DDR3L	800(2)	667	667	Mb/s
DDR2	800(2)	667	667	Mb/s
2:1 Memory Controllers				
DDR3	800(2)	667	667	Mb/s
DDR3L	800(2)	667	667	Mb/s
DDR2	800(2)	667	667	Mb/s
LPDDR2	667	533	533	Mb/s

Notes:

1. V_{REF} tracking is required. For more information, see the *Zynq-7000 AP SoC and 7 Series FPGAs Memory Interface Solutions User Guide* (UG586) [Ref 7].
2. The maximum PHY rate is 667 Mb/s in the FTGB196 package.

IOB Pad Input/Output/3-State

Table 17 summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- T_{IOPI} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HR I/O banks, the IN_TERM termination turn-on time is always faster than T_{IOTP} when the INTERMDISABLE pin is used.

Output Delay Measurements

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in Figure 1 and Figure 2.

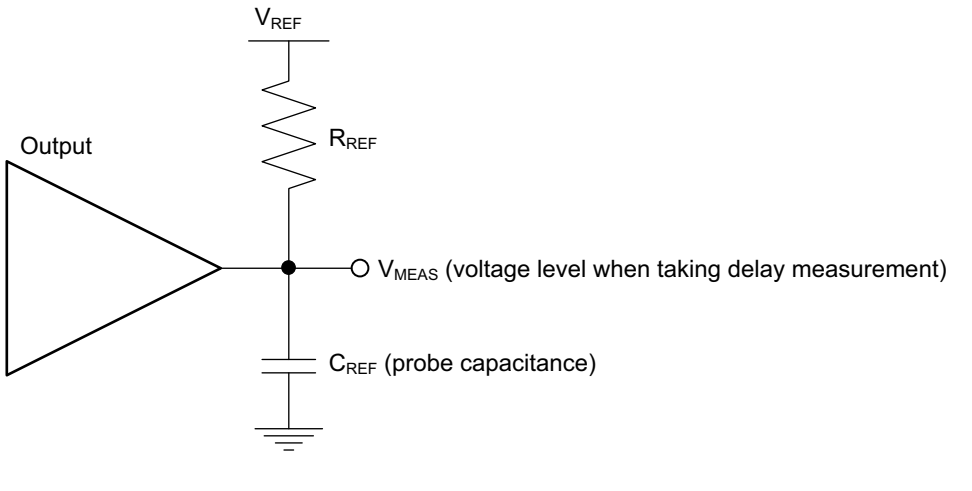

Figure 1: **Single-ended Test Setup**

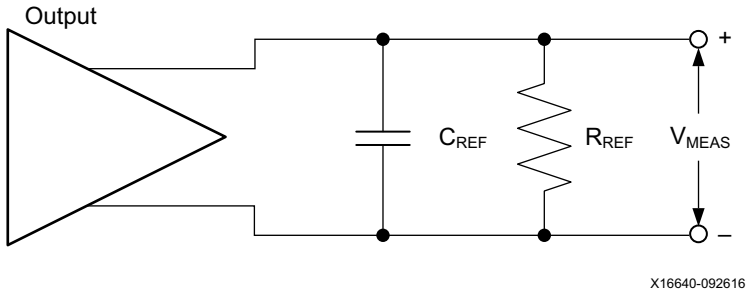

Figure 2: **Differential Test Setup**

Parameters V_{REF}, R_{REF}, C_{REF}, and V_{MEAS} fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using this method:

1. Simulate the output driver of choice into the generalized test setup using values from Table 20.
2. Record the time to V_{MEAS}.
3. Simulate the output driver of choice into the actual PCB trace and load using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to V_{MEAS}.
5. Compare the results of step 2 and step 4. The increase or decrease in delay yields the actual propagation delay of the PCB trace.

Input Serializer/Deserializer Switching Characteristics

Table 23: **ISERDES Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Setup/Hold for Control Lines					
$T_{ISCCK\_BITSLIP}$/ $T_{ISCKC\_BITSLIP}$	BITSLIP pin setup/hold with respect to CLKDIV.	0.02/0.15	0.02/0.17	0.02/0.17	ns
T_{ISCCK_CE}/ T_{ISCKC_CE}	CE pin setup/hold with respect to CLK (for CE1).	0.50/–0.01	0.72/–0.01	0.72/–0.01	ns
T_{ISCCK_CE2}/ T_{ISCKC_CE2}	CE pin setup/hold with respect to CLKDIV (for CE2).	–0.10/0.36	–0.10/0.40	–0.10/0.40	ns
Setup/Hold for Data Lines					
T_{ISDCK_D}/ T_{ISCKD_D}	D pin setup/hold with respect to CLK.	–0.02/0.14	–0.02/0.17	–0.02/0.17	ns
T_{ISDCK_DDLY}/ T_{ISCKD_DDLY}	DDLY pin setup/hold with respect to CLK (using IDELAY).(1)	–0.02/0.14	–0.02/0.17	–0.02/0.17	ns
$T_{ISDCK\_D\_DDR}$/ $T_{ISCKD\_D\_DDR}$	D pin setup/hold with respect to CLK at DDR mode.	–0.02/0.14	–0.02/0.17	–0.02/0.17	ns
$T_{ISDCK\_DDLY\_DDR}$/ $T_{ISCKD\_DDLY\_DDR}$	D pin setup/hold with respect to CLK at DDR mode (using IDELAY).(1)	0.14/0.14	0.17/0.17	0.17/0.17	ns
Sequential Delays					
T_{ISCKO_Q}	CLKDIV to out at Q pin.	0.54	0.66	0.66	ns
Propagation Delays					
T_{ISDO_DO}	D input to DO output pin.	0.11	0.13	0.13	ns

Notes:

1. Recorded at 0 tap value.

Input/Output Delay Switching Characteristics

Table 25: **Input/Output Delay Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
IDELAYCTRL					
T_{DLYCCO_RDY}	Reset to ready for IDELAYCTRL.	3.67	3.67	3.67	µs
$F_{IDELAYCTRL\_REF}$	Attribute REFCLK frequency = 200.00.(1)	200.00	200.00	200.00	MHz
	Attribute REFCLK frequency = 300.00.(1)	300.00	300.00	300.00	MHz
	Attribute REFCLK frequency = 400.00.(1)	400.00	N/A	N/A	MHz
IDELAYCTRL_REF_PRECISION	REFCLK precision	±10	±10	±10	MHz
$T_{IDELAYCTRL\_RPW}$	Minimum reset pulse width.	59.28	59.28	59.28	ns
IDELAY					
$T_{IDELAYRESOLUTION}$	IDELAY chain delay resolution.	1/(32 x 2 x F_{REF})			µs
$T_{IDELAYPAT\_JIT}$	Pattern dependent period jitter in delay chain for clock pattern.(2)	0	0	0	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23).(3)	±5	±5	±5	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23).(4)	±9	±9	±9	ps per tap
$T_{IDELAY\_CLK\_MAX}$	Maximum frequency of CLK input to IDELAY.	680.00	600.00	600.00	MHz
T_{IDCCK_CE} / T_{IDCKC_CE}	CE pin setup/hold with respect to C for IDELAY.	0.16/0.13	0.21/0.16	0.21/0.16	ns
T_{IDCCK_INC}/ T_{IDCKC_INC}	INC pin setup/hold with respect to C for IDELAY.	0.14/0.18	0.16/0.22	0.16/0.22	ns
T_{IDCCK_RST}/ T_{IDCKC_RST}	RST pin setup/hold with respect to C for IDELAY.	0.16/0.11	0.18/0.14	0.18/0.14	ns
$T_{IDDO\_IDATAIN}$	Propagation delay through IDELAY.	Note 5	Note 5	Note 5	ps

Notes:

1. Average tap delay at 200 MHz = 78 ps, at 300 MHz = 52 ps, and at 400 MHz = 39 ps.
2. When HIGH_PERFORMANCE mode is set to TRUE or FALSE.
3. When HIGH_PERFORMANCE mode is set to TRUE.
4. When HIGH_PERFORMANCE mode is set to FALSE.
5. Delay depends on IDELAY tap setting. See the timing report for actual values.

CLB Switching Characteristics

Table 27: **CLB Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Combinatorial Delays					
T_{ILO}	An – Dn LUT address to A.	0.11	0.13	0.13	ns, Max
T_{ILO_2}	An – Dn LUT address to AMUX/CMUX.	0.30	0.36	0.36	ns, Max
T_{ILO_3}	An – Dn LUT address to BMUX_A.	0.46	0.55	0.55	ns, Max
T_{ITO}	An – Dn inputs to A – D Q outputs.	1.05	1.27	1.27	ns, Max
T_{AXA}	AX inputs to AMUX output.	0.69	0.84	0.84	ns, Max
T_{AXB}	AX inputs to BMUX output.	0.66	0.83	0.83	ns, Max
T_{AXC}	AX inputs to CMUX output.	0.68	0.82	0.82	ns, Max
T_{AXD}	AX inputs to DMUX output.	0.75	0.90	0.90	ns, Max
T_{BXB}	BX inputs to BMUX output.	0.57	0.69	0.69	ns, Max
T_{BXD}	BX inputs to DMUX output.	0.69	0.82	0.82	ns, Max
T_{CXC}	CX inputs to CMUX output.	0.48	0.58	0.58	ns, Max
T_{CXD}	CX inputs to DMUX output.	0.59	0.71	0.71	ns, Max
T_{DXD}	DX inputs to DMUX output.	0.58	0.70	0.70	ns, Max
Sequential Delays					
T_{CKO}	Clock to AQ – DQ outputs.	0.44	0.53	0.53	ns, Max
T_{SHCKO}	Clock to AMUX – DMUX outputs.	0.53	0.66	0.66	ns, Max
Setup and Hold Times of CLB Flip-Flops Before/After Clock CLK					
T_{AS}/T_{AH}	AN – DN input to CLK on A – D flip-flops.	0.09/0.14	0.11/0.18	0.11/0.18	ns, Min
T_{DICK}/T_{CKDI}	AX – DX input to CLK on A – D flip-flops.	0.07/0.21	0.09/0.26	0.09/0.26	ns, Min
	AX – DX input through MUXs and/or carry logic to CLK on A – D flip-flops.	0.66/0.09	0.81/0.11	0.81/0.11	ns, Min
$T_{CECK\_CLB}/T_{CKCE\_CLB}$	CE input to CLK on A – D flip-flops.	0.17/0.00	0.21/0.01	0.21/0.01	ns, Min
T_{SRCK}/T_{CKSR}	SR input to CLK on A – D flip-flops.	0.43/0.04	0.53/0.05	0.53/0.05	ns, Min
Set/Reset					
T_{SRMIN}	SR input minimum pulse width.	0.78	1.04	1.04	ns, Min
T_{RQ}	Delay from SR input to AQ – DQ flip-flops.	0.59	0.71	0.71	ns, Max
T_{CEO}	Delay from CE input to AQ – DQ flip-flops.	0.58	0.70	0.70	ns, Max
F_{TOG}	Toggle frequency (for export control).	1286	1098	1098	MHz

Table 30: **Block RAM and FIFO Switching Characteristics *(Cont'd)***

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$T_{RDCK\_DI\_ECC\_FIFO}$/ $T_{RCKD\_DI\_ECC\_FIFO}$	DIN inputs with FIFO ECC in standard mode.(8)	1.15/0.59	1.32/0.64	1.32/0.64	ns, Min
$T_{RCCK\_INJECTBITERR}$/ $T_{RCKC\_INJECTBITERR}$	Inject single/double bit error in ECC mode.	0.64/0.37	0.74/0.40	0.74/0.40	ns, Min
T_{RCCK_EN}/T_{RCKC_EN}	Block RAM enable (EN) input.	0.39/0.21	0.45/0.23	0.45/0.23	ns, Min
T_{RCCK_REGCE}/ T_{RCKC_REGCE}	CE input of output register.	0.29/0.15	0.36/0.16	0.36/0.16	ns, Min
T_{RCCK_RSTREG}/ T_{RCKC_RSTREG}	Synchronous RSTREG input.	0.32/0.07	0.35/0.07	0.35/0.07	ns, Min
T_{RCCK_RSTRAM}/ T_{RCKC_RSTRAM}	Synchronous RSTRAM input.	0.34/0.43	0.36/0.46	0.36/0.46	ns, Min
T_{RCCK_WEA}/T_{RCKC_WEA}	Write enable (WE) input (block RAM only).	0.48/0.19	0.54/0.20	0.54/0.20	ns, Min
T_{RCCK_WREN}/ T_{RCKC_WREN}	WREN FIFO inputs.	0.46/0.35	0.47/0.43	0.47/0.43	ns, Min
T_{RCCK_RDEN}/ T_{RCKC_RDEN}	RDEN FIFO inputs.	0.43/0.35	0.43/0.43	0.43/0.43	ns, Min
Reset Delays					
T_{RCO_FLAGS}	Reset RST to FIFO flags/pointers.(9)	0.98	1.10	1.10	ns, Max
T_{RREC_RST}/T_{RREM_RST}	FIFO reset recovery and removal timing.(10)	2.07/–0.81	2.37/–0.81	2.37/–0.81	ns, Max
Maximum Frequency					
$F_{MAX\_BRAM\_WF\_NC}$	Block RAM (write first and no change modes) when not in SDP RF mode.	460.83	388.20	388.20	MHz
$F_{MAX\_BRAM\_RF\_PERFORMANCE}$	Block RAM (read first, performance mode) when in SDP RF mode but no address overlap between port A and port B.	460.83	388.20	388.20	MHz
$F_{MAX\_BRAM\_RF\_DELAYED\_WRITE}$	Block RAM (read first, delayed write mode) when in SDP RF mode and there is possibility of overlap between port A and port B addresses.	404.53	339.67	339.67	MHz
$F_{MAX\_CAS\_WF\_NC}$	Block RAM cascade (write first, no change mode) when cascade but not in RF mode.	418.59	345.78	345.78	MHz
$F_{MAX\_CAS\_RF\_PERFORMANCE}$	Block RAM cascade (read first, performance mode) when in cascade with RF mode and no possibility of address overlap/one port is disabled.	418.59	345.78	345.78	MHz

Clock Buffers and Networks

Table 32: **Global Clock Switching Characteristics (Including BUFGCTRL)**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$T_{BCCCK\_CE}/T_{BCCKC\_CE}$(1)	CE pins setup/hold.	0.13/0.40	0.16/0.41	0.16/0.41	ns
T_{BCCCK_S}/T_{BCCKC_S}(1)	S pins setup/hold.	0.13/0.40	0.16/0.41	0.16/0.41	ns
T_{BCCKO_O}(2)	BUFGCTRL delay from I0/I1 to O.	0.09	0.10	0.10	ns
Maximum Frequency					
F_{MAX_BUFG}	Global clock tree (BUFG).	628.00	464.00	464.00	MHz

Notes:

1. T_{BCCCK_CE} and T_{BCCKC_CE} must be satisfied to assure glitch-free operation of the global clock when switching between clocks. These parameters do not apply to the BUFGMUX primitive that assures glitch-free operation. The other global clock setup and hold times are optional; only needing to be satisfied if device operation requires simulation matches on a cycle-for-cycle basis when switching between clocks.
2. T_{BGCKO_O} (BUFG delay from I0 to O) values are the same as T_{BCCKO_O} values.

Table 33: **Input/Output Clock Switching Characteristics (BUFIO)**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T_{BIOCKO_O}	Clock to out delay from I to O.	1.26	1.54	1.54	ns
Maximum Frequency					
F_{MAX_BUFIO}	I/O clock tree (BUFIO).	680.00	600.00	600.00	MHz

Table 34: **Regional Clock Buffer Switching Characteristics (BUFR)**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T_{BRCKO_O}	Clock to out delay from I to O.	0.76	0.99	0.99	ns
$T_{BRCKO\_O\_BYP}$	Clock to out delay from I to O with Divide Bypass attribute set.	0.39	0.52	0.52	ns
T_{BRDO_O}	Propagation delay from CLR to O.	0.85	1.09	1.09	ns
Maximum Frequency					
F_{MAX_BUFR}(1)	Regional clock tree (BUFR).	375.00	315.00	315.00	MHz

Notes:

1. The maximum input frequency to the BUFR is the BUFIO F_{MAX} frequency.

Table 37: **MMCM Specification *(Cont'd)***

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$T_{MMCMDCK\_PSINCDEC}$/ $T_{MMCMCKD\_PSINCDEC}$	Setup and hold of phase-shift increment/decrement.	1.04/0.00	1.04/0.00	1.04/0.00	ns
$T_{MMCMCKO\_PSDONE}$	Phase shift clock-to-out of PSDONE.	0.68	0.81	0.81	ns
Dynamic Reconfiguration Port (DRP) for MMCM Before and After DCLK					
$T_{MMCMDCK\_DADDR}$/ $T_{MMCMCKD\_DADDR}$	DADDR setup/hold.	1.40/0.15	1.63/0.15	1.63/0.15	ns, Min
$T_{MMCMDCK\_DI}$/ $T_{MMCMCKD\_DI}$	DI setup/hold.	1.40/0.15	1.63/0.15	1.63/0.15	ns, Min
$T_{MMCMDCK\_DEN}$/ $T_{MMCMCKD\_DEN}$	DEN setup/hold.	1.97/0.00	2.29/0.00	2.29/0.00	ns, Min
$T_{MMCMDCK\_DWE}$/ $T_{MMCMCKD\_DWE}$	DWE setup/hold.	1.40/0.15	1.63/0.15	1.63/0.15	ns, Min
$T_{MMCMCKO\_DRDY}$	CLK to out of DRDY.	0.72	0.99	0.99	ns, Max
F_{DCK}	DCLK frequency.	200.00	200.00	200.00	MHz, Max

Notes:

1. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any MMCM outputs with identical phase.
3. Values for this parameter are available in the *Clocking Wizard* [Ref 8].
4. Includes global clock buffer.
5. Calculated as F_{VCO}/128 assuming output duty cycle is 50%.
6. When CLKOUT4_CASCADE = TRUE, MMCM_F_{OUTMIN} is 0.036 MHz.

PLL Switching Characteristics

Table 38: **PLL Specification**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
PLL_F_{INMAX}	Maximum input clock frequency.	800.00	800.00	800.00	MHz
PLL_F_{INMIN}	Minimum input clock frequency.	19.00	19.00	19.00	MHz
PLL_$F_{INJITTER}$	Maximum input clock period jitter.	< 20% of clock input period or 1 ns Max			
PLL_F_{INDUTY}	Allowable input duty cycle: 19—49 MHz.	25	25	25	%
	Allowable input duty cycle: 50—199 MHz.	30	30	30	%
	Allowable input duty cycle: 200—399 MHz.	35	35	35	%
	Allowable input duty cycle: 400—499 MHz.	40	40	40	%
	Allowable input duty cycle: >500 MHz.	45	45	45	%
PLL_F_{VCOMIN}	Minimum PLL VCO frequency.	800.00	800.00	800.00	MHz
PLL_F_{VCOMAX}	Maximum PLL VCO frequency.	1866.00	1600.00	1600.00	MHz

Table 42: **Clock-Capable Clock Input to Output Delay With PLL(1)**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *with* PLL.						
$T_{ICKOFPLLCC}$	Clock-capable clock input and OUTFF *with* PLL.(2)	XC7S6	0.85	0.85	0.85	ns
		XC7S15	0.85	0.85	0.85	ns
		XC7S25	0.83	0.83	0.83	ns
		XC7S50	0.83	0.83	0.83	ns
		XC7S75	0.83	0.83	0.83	ns
		XC7S100	0.83	0.83	0.83	ns
		XA7S6	0.85	0.85	N/A	ns
		XA7S15	0.85	0.85	N/A	ns
		XA7S25	0.83	0.83	N/A	ns
		XA7S50	0.83	0.83	N/A	ns
		XA7S75	0.83	0.83	N/A	ns
		XA7S100	0.83	0.83	N/A	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. PLL output jitter is already included in the timing calculation.

Table 43: **Pin-to-Pin, Clock-to-Out using BUFIO**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, with BUFIO.					
$T_{ICKOFCS}$	Clock to out of I/O clock.	5.61	6.64	6.64	ns

Table 45: **Clock-Capable Clock Input Setup and Hold With MMCM**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
Input Setup and Hold Time Relative to Global Clock Input Signal for SSTL15 Standard.(1)(2)						
$T_{PSMMCMCC}$/ $T_{PHMMCMCC}$	No delay clock-capable clock input and IFF(3) with MMCM.	XC7S6	2.73/–0.59	3.27/–0.59	3.27/–0.59	ns
		XC7S15	2.73/–0.59	3.27/–0.59	3.27/–0.59	ns
		XC7S25	2.69/–0.61	3.21/–0.61	3.21/–0.61	ns
		XC7S50	2.81/–0.62	3.35/–0.62	3.35/–0.62	ns
		XC7S75	2.81/–0.62	3.36/–0.62	3.36/–0.62	ns
		XC7S100	2.81/–0.62	3.36/–0.62	3.36/–0.62	ns
		XA7S6	2.73/–0.59	3.27/–0.59	N/A	ns
		XA7S15	2.73/–0.59	3.27/–0.59	N/A	ns
		XA7S25	2.69/–0.61	3.21/–0.61	N/A	ns
		XA7S50	2.81/–0.62	3.35/–0.62	N/A	ns
		XA7S75	2.81/–0.62	3.36/–0.62	N/A	ns
		XA7S100	2.81/–0.62	3.36/–0.62	N/A	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, lowest temperature, and highest voltage.
2. Use IBIS to determine any duty-cycle distortion incurred using various standards.
3. IFF = Input flip-flop or latch.

Table 46: **Clock-Capable Clock Input Setup and Hold With PLL**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
Input Setup and Hold Time Relative to Clock-Capable Clock Input Signal for SSTL15 Standard.(1)(2)						
$T_{PSPLLCC}$/ $T_{PHPLLCC}$	No delay clock-capable clock input and IFF(3) with PLL.	XC7S6	3.07/–0.17	3.69/–0.17	3.69/–0.17	ns
		XC7S15	3.07/–0.17	3.69/–0.17	3.69/–0.17	ns
		XC7S25	3.04/–0.19	3.64/–0.19	3.64/–0.19	ns
		XC7S50	3.15/–0.19	3.77/–0.19	3.77/–0.19	ns
		XC7S75	3.15/–0.19	3.78/–0.19	3.78/–0.19	ns
		XC7S100	3.15/–0.19	3.78/–0.19	3.78/–0.19	ns
		XA7S6	3.07/–0.17	3.69/–0.17	N/A	ns
		XA7S15	3.07/–0.17	3.69/–0.17	N/A	ns
		XA7S25	3.04/–0.19	3.64/–0.19	N/A	ns
		XA7S50	3.15/–0.19	3.77/–0.19	N/A	ns
		XA7S75	3.15/–0.19	3.78/–0.19	N/A	ns
		XA7S100	3.15/–0.19	3.78/–0.19	N/A	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, lowest temperature, and highest voltage.
2. Use IBIS to determine any duty-cycle distortion incurred using various standards.
3. IFF = Input flip-flop or latch.

Table 47: **Data Input Setup and Hold Times Relative to a Forwarded Clock Input Pin Using BUFIO**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Input Setup and Hold Time Relative to a Forwarded Clock Input Pin Using BUFIO for SSTL15 Standard.					
T_{PSCS}/T_{PHCS}	Setup and hold of I/O clock.	–0.38/1.46	–0.38/1.73	–0.38/1.76	ns

Table 48: **Sample Window**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T_{SAMP}	Sampling error at receiver pins.(1)	0.64	0.70	0.70	ns
T_{SAMP_BUFIO}	Sampling error at receiver pins using BUFIO.(2)	0.40	0.46	0.46	ns

Notes:

1. This parameter indicates the total sampling error of the Spartan-7 FPGAs DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the MMCM to capture the DDR input registers' edges of operation. These measurements include:
   - CLK0 MMCM jitter
   - MMCM accuracy (phase offset)
   - MMCM phase shift resolution

   These measurements do not include package or clock tree skew.
2. This parameter indicates the total sampling error of the Spartan-7 FPGAs DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the BUFIO clock network and IDELAY to capture the DDR input registers' edges of operation. These measurements do not include package or clock tree skew.

XADC Specifications

The *7 Series FPGAs Overview* (DS180) [Ref 1] and *XA Spartan-7 Automotive FPGA Data Sheet: Overview* (DS171) [Ref 2] list the devices that contain a 7 series XADC dual 12-Bit 1 MSPS analog-to-digital converter.

Table 50: **XADC Specifications**

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
V_{CCADC} = 1.8V ± 5%, V_{REFP} = 1.25V, V_{REFN} = 0V, ADCCLK = 26 MHz, –55°C ≤ T_j ≤ 125°C. Typical values at T_j = +40°C.						
ADC Accuracy(1)						
Resolution			12	–	–	Bits
Integral nonlinearity(2)	INL	–40°C ≤ T_j ≤ 100°C	–	–	±2	LSBs
		–55°C ≤ T_j < –40°C; 100°C < T_j ≤ 125°C	–	–	±3	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic.	–	–	±1	LSBs
Offset error	Unipolar	–40°C ≤ T_j ≤ 100°C	–	–	±8	LSBs
		–55°C ≤ T_j < –40°C; 100°C < T_j ≤ 125°C	–	–	±12	LSBs
	Bipolar	–55°C ≤ T_j ≤ 125°C	–	–	±4	LSBs
Gain error			–	–	±0.5	%
Offset matching			–	–	4	LSBs
Gain matching			–	–	0.3	%
Sample rate			–	–	1	MS/s
Signal to noise ratio(2)	SNR	F_{SAMPLE} = 500 KS/s, F_{IN} = 20 kHz	60	–	–	dB
RMS code noise		External 1.25V reference.	–	–	2	LSBs
		On-chip reference.	–	3	–	LSBs
Total harmonic distortion(2)	THD	F_{SAMPLE} = 500 KS/s, F_{IN} = 20 kHz	70	–	–	dB
Analog Inputs(3)						
ADC input ranges		Unipolar operation.	0	–	1	V
		Bipolar operation.	–0.5	–	+0.5	V
		Unipolar common mode range (FS input).	0	–	+0.5	V
		Bipolar common mode range (FS input).	+0.5	–	+0.6	V
Maximum external channel input ranges		Adjacent analog channels set within these ranges should not corrupt measurements on adjacent channels.	–0.1	–	V_{CCADC}	V
Full-resolution bandwidth	FRBW	Auxiliary channel full resolution bandwidth.	250	–	–	kHz
On-chip Sensors						
Temperature sensor error		–40°C ≤ T_j ≤ 100°C	–	–	±4	°C
		–55°C ≤ T_j < –40°C; 100°C < T_j ≤ 125°C	–	–	±6	°C
Supply sensor error		–40°C ≤ T_j ≤ 100°C	–	–	±1	%
		–55°C ≤ T_j < –40°C; 100°C < T_j ≤ 125°C	–	–	±2	%

Table 50: **XADC Specifications *(Cont'd)***

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
Conversion Rate(4)						
Conversion time: continuous	t_{CONV}	Number of ADCCLK cycles.	26	–	32	Cycles
Conversion time: event	t_{CONV}	Number of CLK cycles.	–	–	21	Cycles
DRP clock frequency	DCLK	DRP clock frequency.	8	–	250	MHz
ADC clock frequency	ADCCLK	Derived from DCLK.	1	–	26	MHz
DCLK duty cycle			40	–	60	%
XADC Reference(5)						
External reference	V_{REFP}	Externally supplied reference voltage.	1.20	1.25	1.30	V
On-chip reference		Ground V_{REFP} pin to AGND, $-40°C \le T_j \le 100°C$	1.2375	1.25	1.2625	V
		Ground VREFP pin to AGND, $-55°C \le T_j < -40°C$; $100°C < T_j \le 125°C$	1.225	1.25	1.275	V

Notes:

1. Offset and gain errors are removed by enabling the XADC automatic gain calibration feature. The values are specified for when this feature is enabled.
2. Only specified for bitstream option XADCEnhancedLinearity = ON.
3. For a detailed description, see the *ADC* chapter in the *7 Series FPGAs and Zynq-7000 AP SoC XADC Dual 12-Bit 1 MSPS Analog-to-Digital Converter User Guide* (UG480) [Ref 9].
4. For a detailed description, see the *Timing* chapter in the *7 Series FPGAs and Zynq-7000 AP SoC XADC Dual 12-Bit 1 MSPS Analog-to-Digital Converter User Guide* (UG480) [Ref 9].
5. Any variation in the reference voltage from the nominal V_{REFP} = 1.25V and V_{REFN} = 0V will result in a deviation from the ideal transfer function. This also impacts the accuracy of the internal sensor measurements (i.e., temperature and power supply). However, for external ratiometric type applications allowing reference to vary by ±4% is permitted.

eFUSE Programming Conditions

Table 52 lists the programming conditions specifically for eFUSE. For more information, see the *7 Series FPGA Configuration User Guide* (UG470) [Ref 10].

Table 52: **eFUSE Programming Conditions(1)**

Symbol	Description	Min	Typ	Max	Units
I_{FS}	V_{CCAUX} supply current	–	–	115	mA
T_j	Temperature range	15	–	125	°C

Notes:

1. The FPGA must not be configured during eFUSE programming.

References

1. *7 Series FPGAs Overview* (DS180)
2. *XA Spartan-7 Automotive FPGA Data Sheet: Overview* (DS171)
3. *7 Series FPGAs SelectIO Resources User Guide* (UG471)
4. *7 Series FPGA Packaging and Pinout Specification* (UG475)
5. *7 Series FPGAs PCB Design Guide* (UG483)
6. *Xilinx Power Estimator* spreadsheet tool (XPE)
7. *Zynq-7000 AP SoC and 7 Series FPGAs Memory Interface Solutions User Guide* (UG586)
8. See the Clocking Wizard in Vivado software.
9. *7 Series FPGAs and Zynq-7000 AP SoC XADC Dual 12-Bit 1 MSPS Analog-to-Digital Converter User Guide* (UG480)
10. *7 Series FPGA Configuration User Guide* (UG470)

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